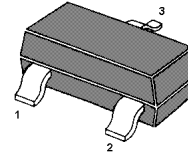


BCW30

PNP Silicon Epitaxial Planar Transistor

general purpose switching and amplification



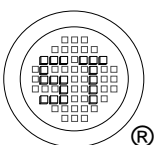
1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CB0}$	32	V
Collector Emitter Voltage	$-V_{CEO}$	32	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	100	mA
Peak Collector Current	$-I_{CM}$	200	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 5\text{ V}$, $-I_C = 2\text{ mA}$	h_{FE}	215	-	500	-
Collector Base Cutoff Current at $-V_{CB} = 30\text{ V}$	$-I_{CBO}$	-	-	100	nA
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	-	100	nA
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	32	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	32	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 10\text{ mA}$, $-I_B = 0.5\text{ mA}$	$-V_{CE(sat)}$	-	-	0.3	V
Base Emitter Voltage at $-V_{CE} = 5\text{ V}$, $-I_C = 2\text{ mA}$	$-V_{BE(on)}$	0.6	-	0.75	V
Transition Frequency at $-V_{CE} = 5\text{ V}$, $I_E = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	100	-	-	MHz
Collector Base Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	4.5	-	pF



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